

Product Summary

| $V_{(BR)DSS}$ | $R_{DS(ON) \max}$ | $I_{D \max}$ $T_A = +25^\circ\text{C}$ |
|---------------|--------------------------------|---|
| 20V | 9.5mΩ @ $V_{GS} = 4.5\text{V}$ | 11.7A |
| | 11mΩ @ $V_{GS} = 2.5\text{V}$ | 10.8A |

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- General Purpose Interfacing Switch
- Power Management Functions

Features

- 0.6mm Profile – Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- Low On-Resistance
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. “Green” Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

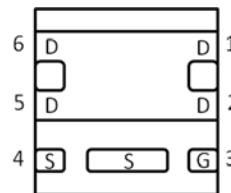
- Case: U-DFN2020-6
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e4)
- Weight: 0.0065 grams (Approximate)



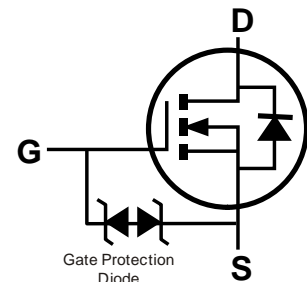
ESD PROTECTED



Bottom View



Bottom View
Pin Out



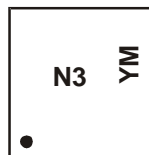
Equivalent Circuit

Ordering Information (Note 4)

| Part Number | Marking | Reel size (inches) | Quantity per reel |
|----------------|---------|--------------------|-------------------|
| DMN2011UFDE-7 | N3 | 7 | 3,000 |
| DMN2011UFDE-13 | N3 | 13 | 10,000 |

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 - See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



N3 = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: A = 2013)
M = Month (ex: 9 = September)

Date Code Key

| Year | 2011 | 2012 | 2013 | 2014 | 2015 | 2016 | 2017 |
|------|------|------|------|------|------|------|------|
| Code | Y | Z | A | B | C | D | E |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | O | N | D |

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Units |
|--|--------------|--|------------------|--------------|-------|
| Drain-Source Voltage | | | V _{DSS} | 20 | V |
| Gate-Source Voltage | | | V _{GSS} | ±12 | V |
| Continuous Drain Current (Note 6) V _{GS} = 4.5V | Steady State | T _A = +25°C T _A = +70°C | I _D | 11.7 9.3 | A |
| | t < 10s | T _A = +25°C T _A = +70°C | I _D | 14.2 11.4 | A |
| Continuous Drain Current (Note 6) V _{GS} = 2.5V | Steady State | T _A = +25°C T _A = +70°C | I _D | 10.8 8.7 | A |
| | t < 10s | T _A = +25°C T _A = +70°C | I _D | 13.2 10.6 | A |
| Pulsed Drain Current (10µs pulse, duty cycle = 1%) | | | I _{DM} | 80 | A |
| Maximum Body Diode Continuous Current | | | I _S | 2.5 | A |
| Avalanche Current (Note 7) L = 0.1mH | | | I _{AS} | 18 | A |
| Avalanche Energy (Note 7) L = 0.1mH | | | E _{AS} | 17 | mJ |

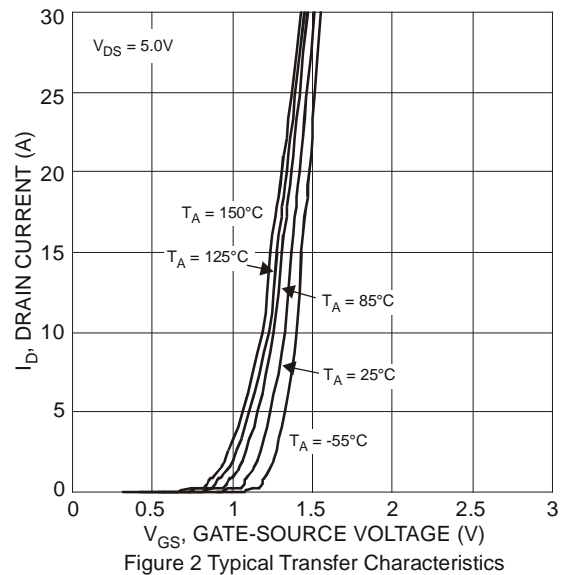
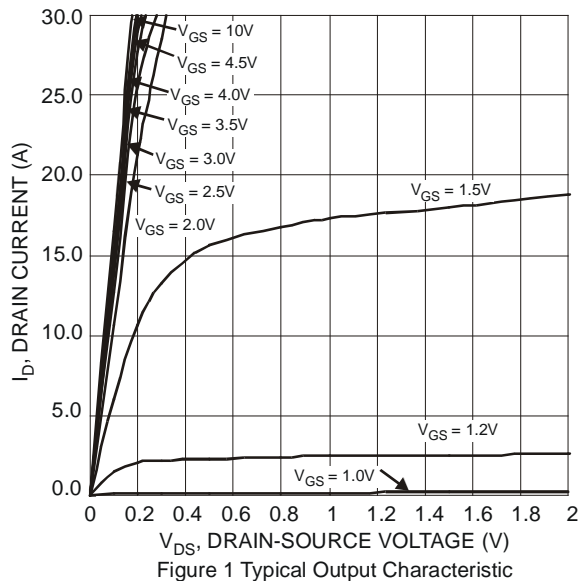
Thermal Characteristics

| Characteristic | | Symbol | Value | Units |
|--|------------------------|-----------------------------------|-------------|-------|
| Total Power Dissipation (Note 5) | T _A = +25°C | P _D | 0.61 | W |
| | T _A = +70°C | | 0.39 | |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady state | R _{θJA} | 209 | °C/W |
| | t < 10s | | 142 | |
| Total Power Dissipation (Note 6) | T _A = +25°C | P _D | 1.97 | W |
| | T _A = +70°C | | 1.27 | |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady state | R _{θJA} | 64 | °C/W |
| | t < 10s | | 43 | |
| Thermal Resistance, Junction to Case (Note 6) | | R _{θJC} | 9.8 | |
| Operating and Storage Temperature Range | | T _J , T _{STG} | -55 to +150 | °C |

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|--|---------------------|-----|------|------|------|---|
| OFF CHARACTERISTICS (Note 8) | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 20 | — | — | V | V _{GS} = 0V, I _D = 250μA |
| Zero Gate Voltage Drain Current T _J = +25°C | I _{DSS} | — | — | 1 | μA | V _{DS} = 16V, V _{GS} = 0V |
| Zero Gate Voltage Drain Current T _J = +150°C (Note 9) | I _{DSS} | — | — | 100 | μA | V _{DS} = 16V, V _{GS} = 0V |
| Gate-Source Leakage | I _{GSS} | — | — | ±10 | μA | V _{GS} = ±10V, V _{DS} = 0V |
| ON CHARACTERISTICS (Note 8) | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | 0.4 | — | 1.0 | V | V _{DS} = V _{GS} , I _D = 250μA |
| Static Drain-Source On-Resistance | R _{DS(on)} | — | 6.5 | 9.5 | mΩ | V _{GS} = 4.5V, I _D = 7A |
| | | | 7.5 | 11 | | V _{GS} = 2.5V, I _D = 7A |
| | | | 10 | 20 | | V _{GS} = 1.8V, I _D = 5A |
| | | | 15 | 35 | | V _{GS} = 1.5V, I _D = 3A |
| Diode Forward Voltage | V _{SD} | — | 0.7 | 1.2 | V | V _{GS} = 0V, I _S = 8.5A |
| On State Drain Current (Note 9) | I _{D(on)} | 20 | — | — | A | V _{DS} ≤ 5V, V _{GS} = 4.5V |
| DYNAMIC CHARACTERISTICS (Note 9) | | | | | | |
| Input Capacitance | C _{iss} | — | 2248 | 3372 | pF | V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz |
| Output Capacitance | C _{oss} | — | 295 | 443 | pF | |
| Reverse Transfer Capacitance | C _{rss} | — | 265 | 398 | pF | |
| Gate Resistance | R _g | — | 1.5 | 3 | Ω | V _{DS} = 0V, V _{GS} = 0V, f = 1MHz |
| Total Gate Charge (V _{GS} = 4.5V) | Q _g | — | 24 | 36 | nC | V _{DS} = 10V, I _D = 8.5A |
| Total Gate Charge (V _{GS} = 10V) | Q _g | — | 56 | 84 | nC | |
| Gate-Source Charge | Q _{gs} | — | 3.5 | 6 | nC | |
| Gate-Drain Charge | Q _{gd} | — | 5.1 | 8 | nC | |
| Turn-On Delay Time | t _{D(on)} | — | 3.6 | 6 | ns | V _{DS} = 10V, I _D = 8.5A V _{GS} = 4.5V, R _G = 1.8Ω |
| Turn-On Rise Time | t _r | — | 2.6 | 4 | ns | |
| Turn-Off Delay Time | t _{D(off)} | — | 21.6 | 33 | ns | |
| Turn-Off Fall Time | t _f | — | 13.5 | 21 | ns | I _F = 8.5A, di/dt = 210A/μs |
| Reverse Recovery Time | T _{rr} | — | 12.8 | 20 | ns | |
| Reverse Recovery Charge | Q _{rr} | — | 6.9 | 11 | nC | |

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to product testing.



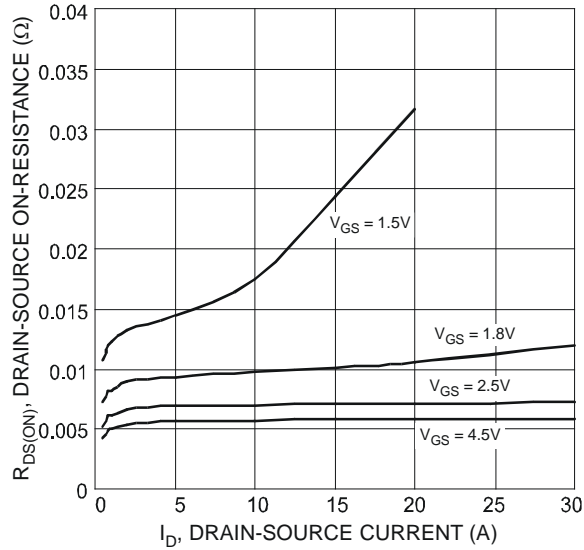


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

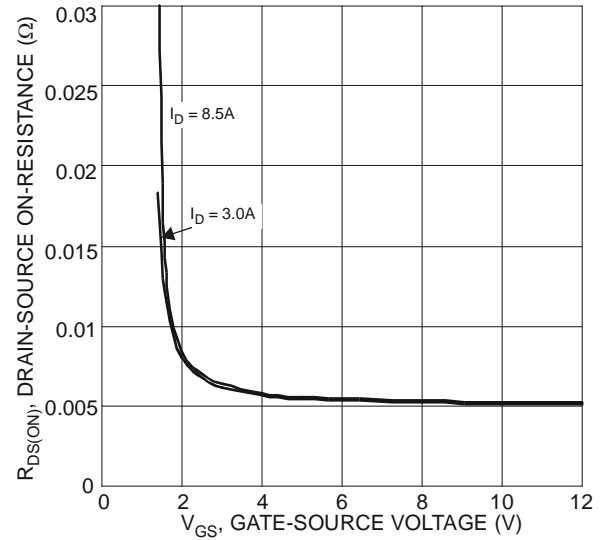


Figure 4 Typical Transfer Characteristics

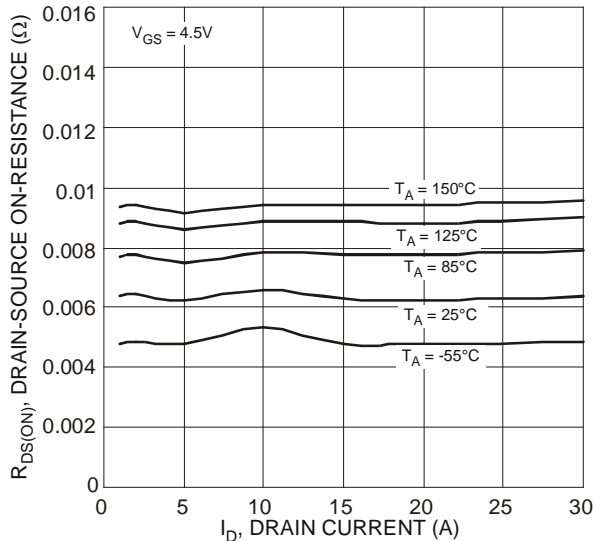


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

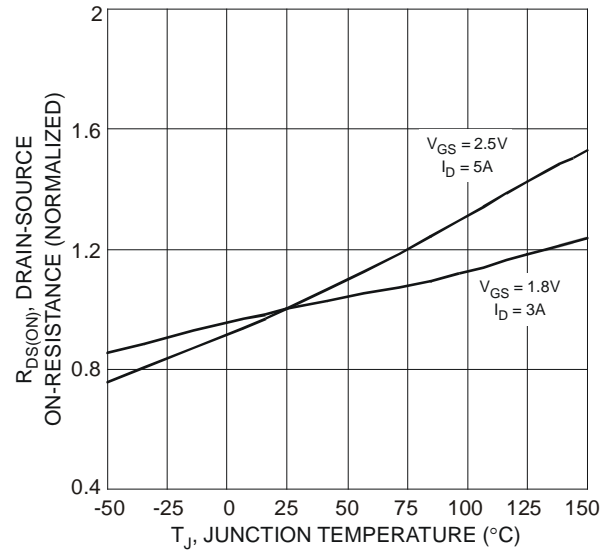


Figure 6 On-Resistance Variation with Temperature

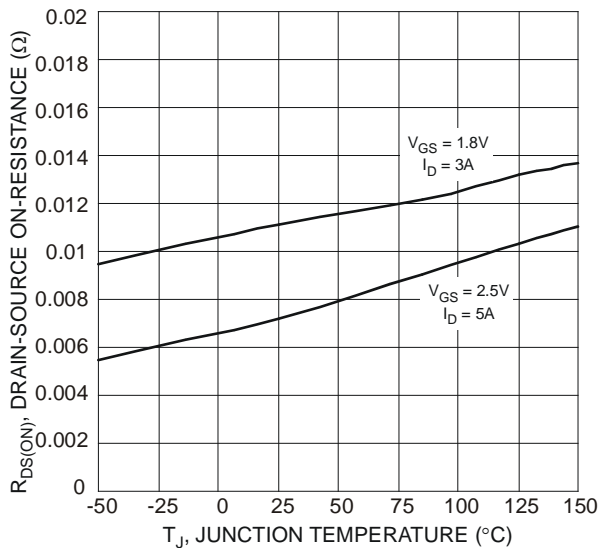


Figure 7 On-Resistance Variation with Temperature

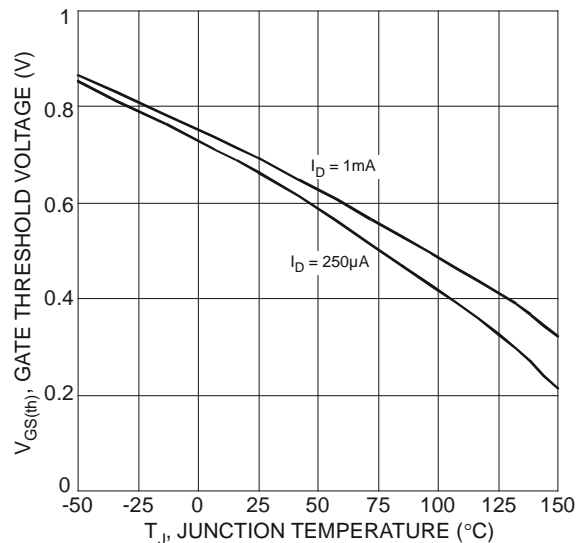
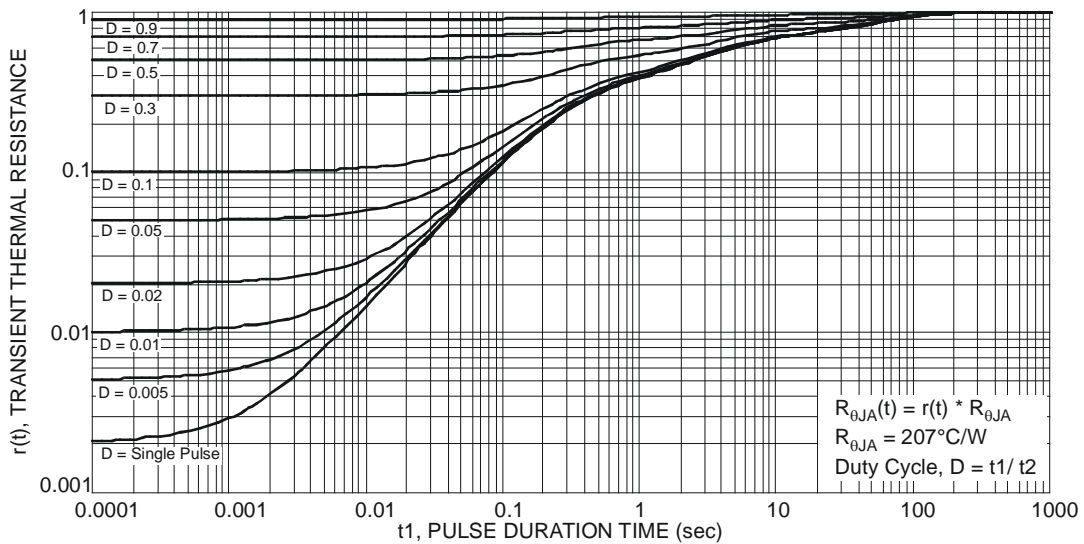
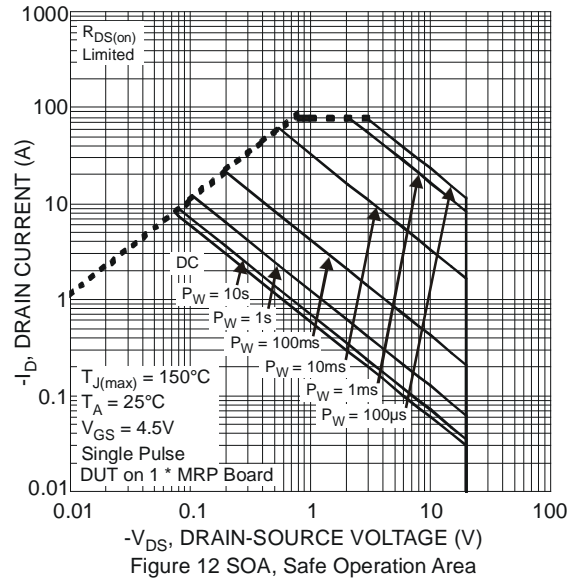
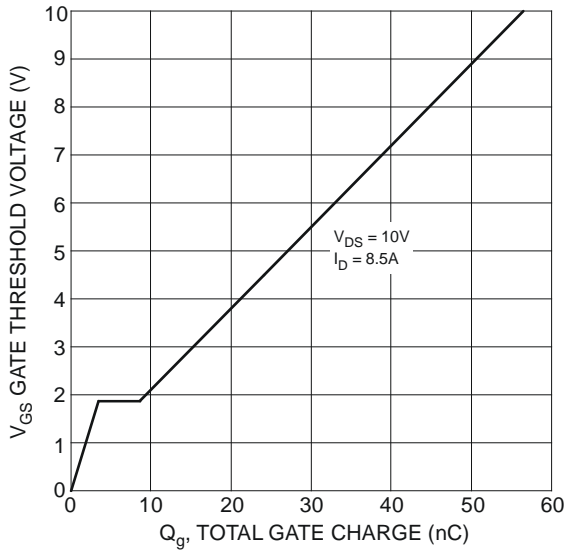
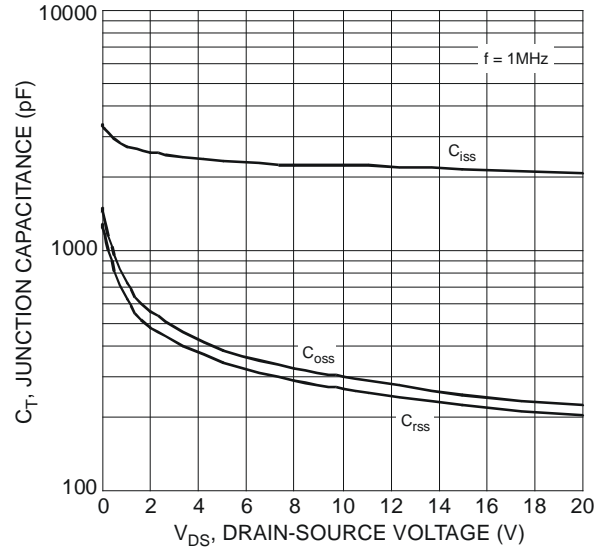
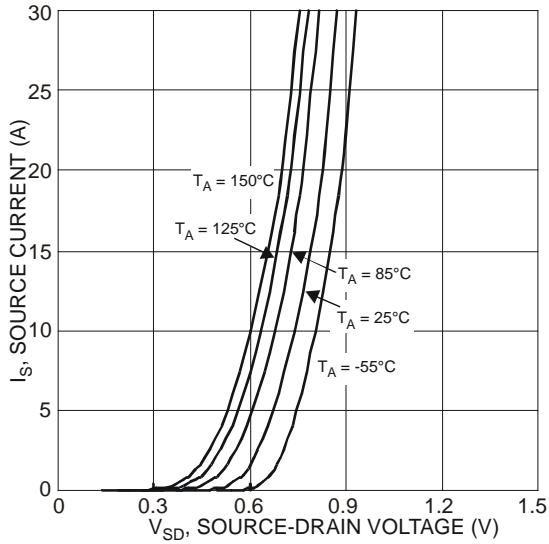
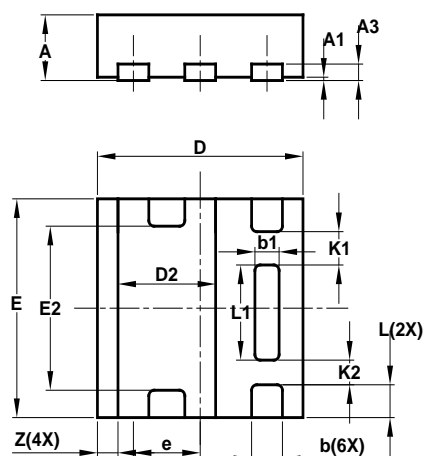


Figure 8 Gate Threshold Variation vs. Ambient Temperature



Package Outline Dimensions

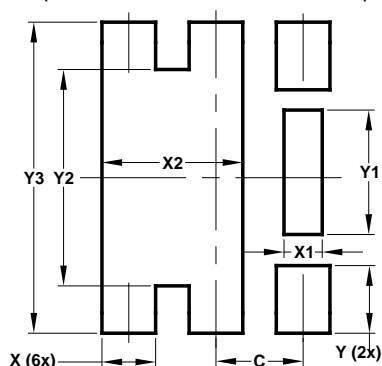
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



| U-DFN2020-6 Type E | | | |
|-----------------------|-------|-------|-------|
| Dim | Min | Max | Typ |
| A | 0.57 | 0.63 | 0.60 |
| A1 | 0 | 0.05 | 0.03 |
| A3 | — | — | 0.15 |
| b | 0.25 | 0.35 | 0.30 |
| b1 | 0.185 | 0.285 | 0.235 |
| D | 1.95 | 2.05 | 2.00 |
| D2 | 0.85 | 1.05 | 0.95 |
| E | 1.95 | 2.05 | 2.00 |
| E2 | 1.40 | 1.60 | 1.50 |
| e | — | — | 0.65 |
| L | 0.25 | 0.35 | 0.30 |
| L1 | 0.82 | 0.92 | 0.87 |
| K1 | — | — | 0.305 |
| K2 | — | — | 0.225 |
| Z | — | — | 0.20 |
| All Dimensions in mm | | | |

Suggested Pad Layout

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



| Dimensions | Value (in mm) |
|------------|------------------|
| C | 0.650 |
| X | 0.400 |
| X1 | 0.285 |
| X2 | 1.050 |
| Y | 0.500 |
| Y1 | 0.920 |
| Y2 | 1.600 |
| Y3 | 2.300 |

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